

Supporting Information

Interfacial reconstruction in the $La_{0.7}Sr_{0.3}MnO_3$ thin films: giant low-field magnetoresistance.

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The substrate LaAlO_3 (LAO) is cubic at temperature $> 800^\circ\text{C}$ with space group $Pm\bar{3}m$.¹ On cooling the substrate below 800°C , the crystals structure of the LAO becomes rhombohedral with the space group $R\bar{3}C$.² The structure of LAO at room temperature provides a simple example of octahedral tilting. The AlO_6 tilting can be described by using Glazer³ symbols of the form $a^\#b^\#c^\#$ in which the literals refer in turn to tilts around axes in the x, y and z directions of the $Pm\bar{3}m$ parent structure. The repetition of a letter indicates that the tilts about the corresponding axes are equal in magnitude. The superscript $\#$ takes the value $+$ or $-$ to indicate that the tilts of successive octahedra along the relevant axis are in the same or opposite sense. The terms in-phase (Fig. S1(a)) tilting to describe the former case ($+$) and out-of-phase (Fig. S1(b)) tilting for the latter ($-$). For directions about which there is no octahedral tilting, we show the superscript $\#$ as 0. Thus, the LAO at temperature $> 800^\circ\text{C}$ exhibits $a^0b^0c^0$ with lattice parameter $3.81\text{ \AA}$,¹ but transform to $a^-b^-c^-$ with lattice parameter $5.36\text{ \AA}$ (i.e., Pseudo-cubic lattice parameter $3.79\text{ \AA}$).²

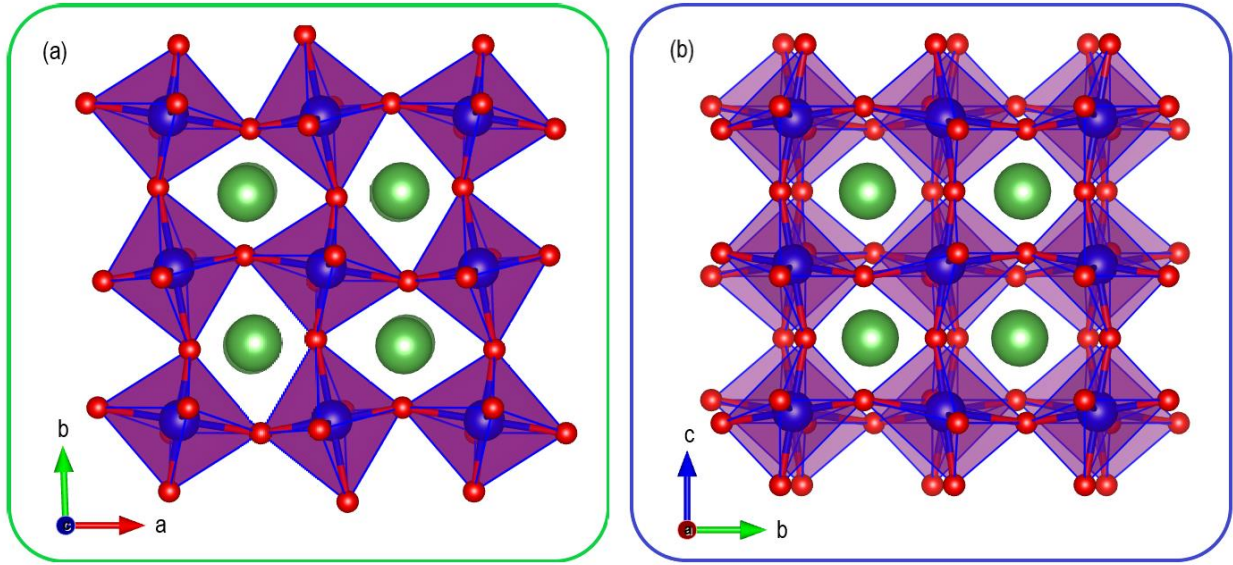


Fig. S1. Schematic for the (a) in-phase and (b) out-of-phase rotation of the MnO_6 in manganites.

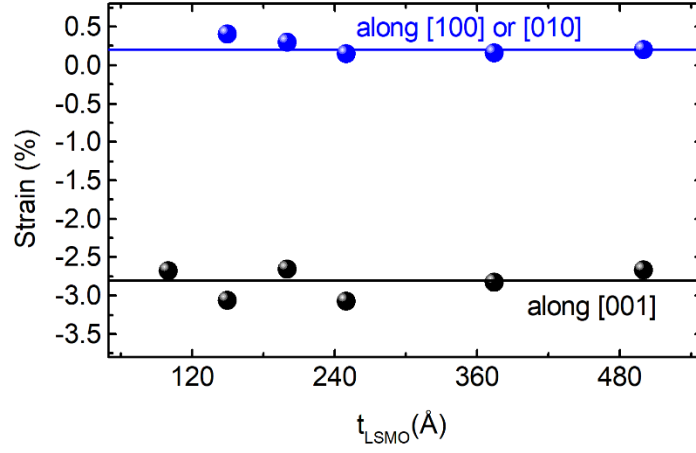


Fig. S2. Strain along the [100] or [010] and [001] of different $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ films grown on (001) oriented LaAlO_3 .

The strain on the LSMO thin films grown on (001) LaAlO_3 is calculated using the relations

$$\frac{a_{\text{bulk}} - a_{\text{film}}}{a_{\text{bulk}}} \times 100 \quad \text{or} \quad \frac{a_{\text{bulk}} - c_{\text{film}}}{a_{\text{bulk}}} \times 100.$$

Fig. S2 shows the in-plane and out-of-plane strain calculated using the (101) and (001) x-ray diffraction scans of the LSMO thin films.

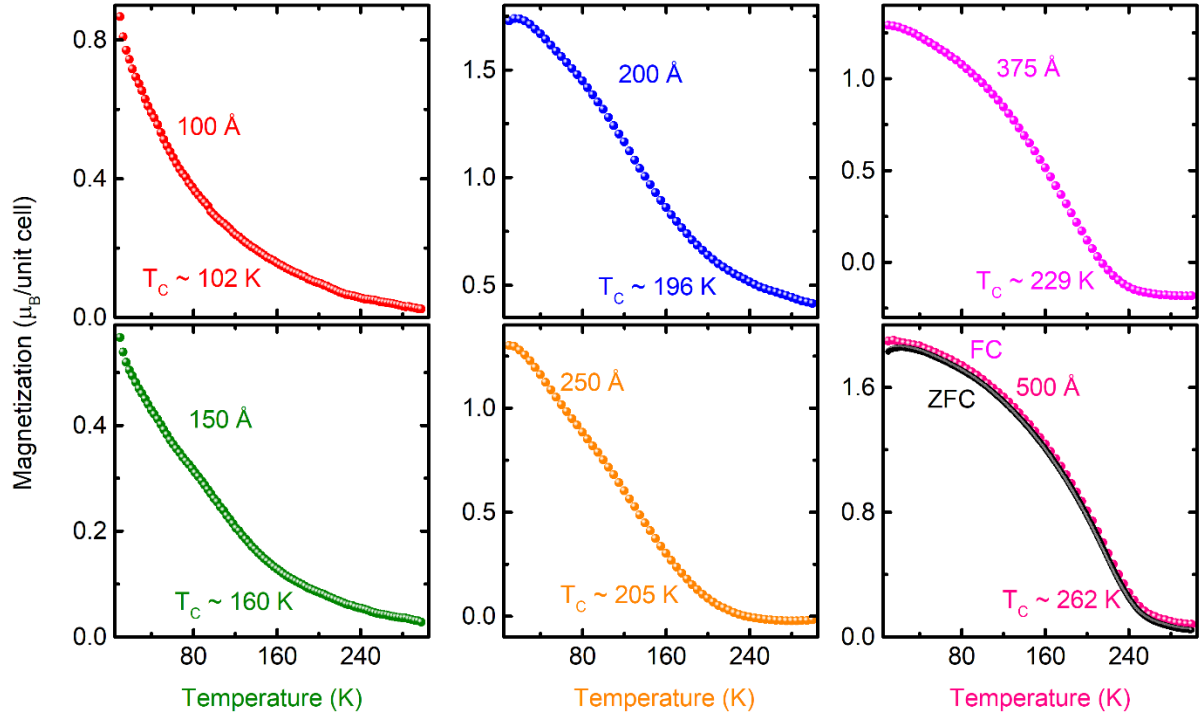


Fig. S3. Temperature-dependent 0.5 T field-cooled magnetization of the 100 Å, 150 Å, 200 Å, 250 Å, 375 Å, and 500 Å thick $La_{0.7}Sr_{0.3}MnO_3$ films grown on (001) oriented $LaAlO_3$. The zero-field-cooled magnetization of the 500 Å thick $La_{0.7}Sr_{0.3}MnO_3$ films is also shown in lower right panel.

Fig. S3 shows the temperature-dependent magnetization of the LSMO thin films with various thicknesses. The Curie temperature of these LSMO films decreases with a decrease in thickness. The T_c of the LSMO films was determined from the intersection of the straight lines, which fit the magnetization on either side of the onset of the ferromagnetic state temperature⁴.

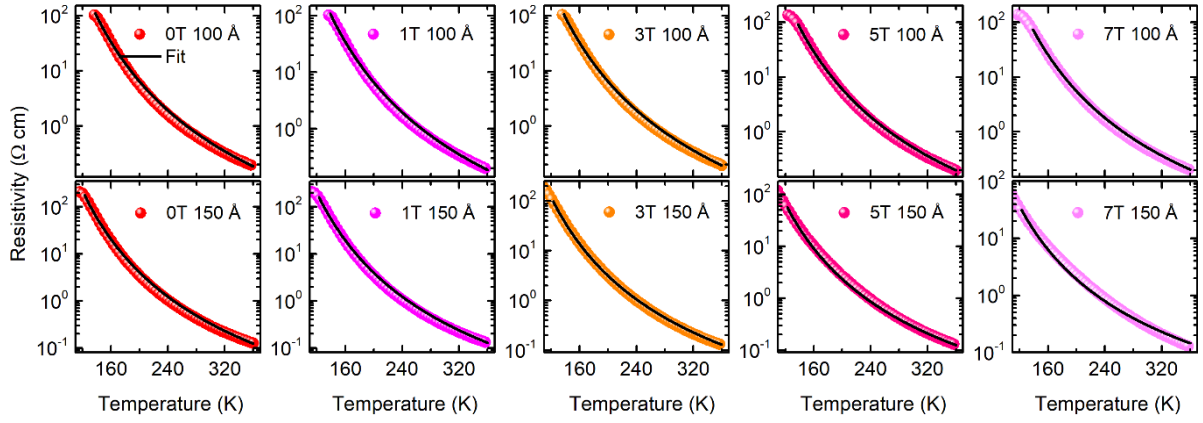


Fig. S4. Temperature-dependent resistivity, measured in the presence of 0, 1, 3, 5, and 7 T magnetic fields, for the 100 Å, and 150 Å thick $La_{0.7}Sr_{0.3}MnO_3$ films grown on (001) oriented $LaAlO_3$. The solid line represents the fit to the Efros-Shklovskii variable range hopping model.

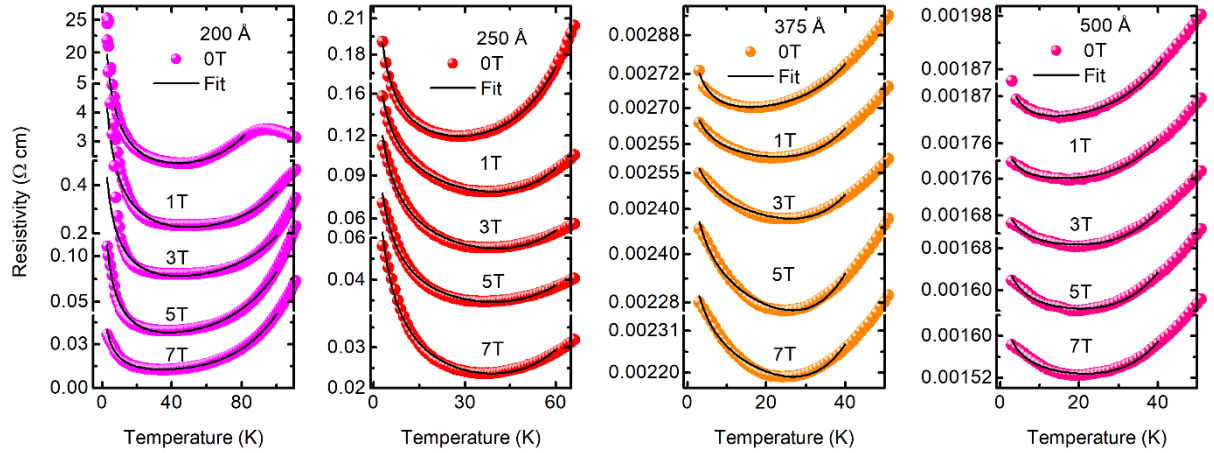


Fig. S5. Temperature-dependent resistivity, measured in the presence of 0, 1, 3, 5, and 7 T magnetic fields, for the 200 Å, 250 Å, 375 Å, and 500 Å thick $La_{0.7}Sr_{0.3}MnO_3$ films grown on (001) oriented $LaAlO_3$. The solid lines are the fit to the low-temperature resistivity using Eq. 2.

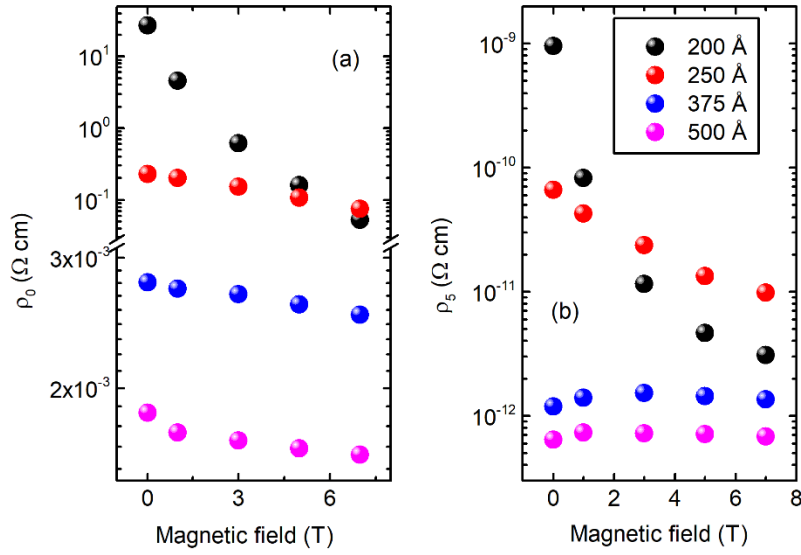


Fig. S6. Magnetic field dependent fitting parameters (a) ρ_0 and (b) ρ_5 of Eq. 2 for the 200 Å, 250 Å, 375 Å, and 500 Å thick $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ films grown on (001) oriented LaAlO_3 .

References :

- 1 S. Geller, and P. M. Raccah, *Phys. Rev. B*, 1970, **2**, 1167.
- 2 G. W. Berkstresser, A. J. Valentino, and C. D. Brandle, *J. Cryst. Growth*, 1991, **109**, 457.
- 3 A. M. Glazer, *Acta Cryst. B*, 1972, **28**, 3384.
- 4 R. López-Ruiz, C. Magén, F. Luis, and J. Bartolomé, *J. Appl. Phys.*, 2012, **112**, 073906.